

MJE2955T (PNP) MJE3055T (NPN)

Preferred Device

Complementary Silicon Plastic Power Transistors

These devices are designed for use in general-purpose amplifier and switching applications.

Features

- DC Current Gain Specified to 10 A
- High Current Gain - Bandwidth Product -
 $f_T = 2.0 \text{ MHz (Min) @ } I_C$
 $= 500 \text{ mAdc}$
- Pb-Free Packages are Available*

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector-Emitter Voltage	V_{CEO}	60	Vdc
Collector-Base Voltage	V_{CB}	70	Vdc
Emitter-Base Voltage	V_{EB}	5.0	Vdc
Collector Current	I_C	10	Adc
Base Current	I_B	6.0	Adc
Total Device Dissipation @ $T_C = 25^\circ\text{C}$ Derate above 25°C	P_D (Note 1)	75 0.6	W W/ $^\circ\text{C}$
Operating and Storage Junction Temperature Range	T_J, T_{stg}	-55 to +150	$^\circ\text{C}$

THERMAL CHARACTERISTICS

Characteristics	Symbol	Max	Unit
Thermal Resistance, Junction-to-Case	θ_{JC}	1.67	$^\circ\text{C/W}$

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

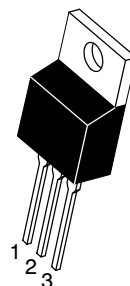
1. Safe Area Curves are indicated by Figure 1. Both limits are applicable and must be observed.

*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.



ON Semiconductor®

10 AMPERE COMPLEMENTARY SILICON POWER TRANSISTORS 60 VOLTS - 75 WATTS



TO-220AB
CASE 221A-09
STYLE 1

MARKING DIAGRAM



MJExx55 = Device Code
 xx = 29 or 30
 G = Pb-Free Package
 A = Assembly Location
 Y = Year
 WW = Work Week

ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 3 of this data sheet.

Preferred devices are recommended choices for future use and best overall value.

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ELECTRICAL CHARACTERISTICS ($T_C = 25^\circ\text{C}$ unless otherwise noted)

Characteristic	Symbol	Min	Max	Unit
OFF CHARACTERISTICS				
Collector-Emitter Sustaining Voltage (Note 2) ($I_C = 200\text{ mAdc}$, $I_B = 0$)	$V_{CEO(sus)}$	60	-	Vdc
Collector Cutoff Current ($V_{CE} = 30\text{ Vdc}$, $I_B = 0$)	I_{CEO}	-	700	μAdc
Collector Cutoff Current ($V_{CE} = 70\text{ Vdc}$, $V_{EB(off)} = 1.5\text{ Vdc}$) ($V_{CE} = 70\text{ Vdc}$, $V_{EB(off)} = 1.5\text{ Vdc}$, $T_C = 150^\circ\text{C}$)	I_{CEX}	-	1.0 5.0	mAdc
Collector Cutoff Current ($V_{CB} = 70\text{ Vdc}$, $I_E = 0$) ($V_{CB} = 70\text{ Vdc}$, $I_E = 0$, $T_C = 150^\circ\text{C}$)	I_{CBO}	-	1.0 10	mAdc
Emitter Cutoff Current ($V_{BE} = 5.0\text{ Vdc}$, $I_C = 0$)	I_{EBO}	-	5.0	mAdc
ON CHARACTERISTICS				
DC Current Gain (Note 2) ($I_C = 4.0\text{ Adc}$, $V_{CE} = 4.0\text{ Vdc}$) ($I_C = 10\text{ Adc}$, $V_{CE} = 4.0\text{ Vdc}$)	h_{FE}	20 5.0	100 -	-
Collector-Emitter Saturation Voltage (Note 2) ($I_C = 4.0\text{ Adc}$, $I_B = 0.4\text{ Adc}$) ($I_C = 10\text{ Adc}$, $I_B = 3.3\text{ Adc}$)	$V_{CE(sat)}$	-	1.1 8.0	Vdc
Base-Emitter On Voltage (Note 2) ($I_C = 4.0\text{ Adc}$, $V_{CE} = 4.0\text{ Vdc}$)	$V_{BE(on)}$	-	1.8	Vdc
DYNAMIC CHARACTERISTICS				
Current-Gain-Bandwidth Product ($I_C = 500\text{ mAdc}$, $V_{CE} = 10\text{ Vdc}$, $f = 500\text{ kHz}$)	f_T	2.0	-	MHz

2. Pulse Test: Pulse Width $\leq 300\ \mu\text{s}$, Duty Cycle $\leq 20\%$.

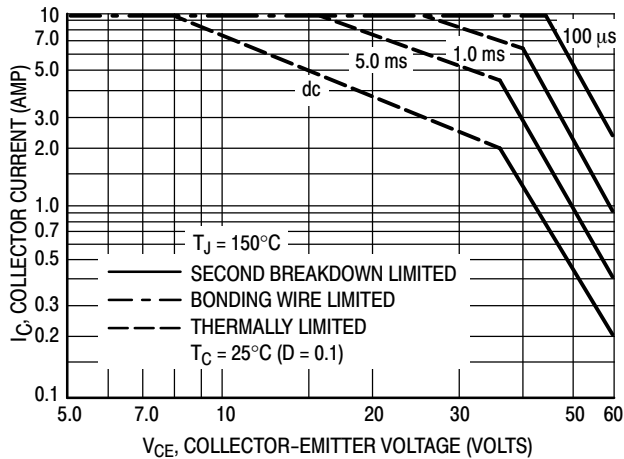


Figure 1. Active-Region Safe Operating Area

There are two limitations on the power handling ability of a transistor: average junction temperature and second breakdown. Safe operating area curves indicate $I_C - V_{CE}$ limits of the transistor that must be observed for reliable operation; i.e., the transistor must not be subjected to greater dissipation than the curves indicate.

The data of Figure 1 is based on $T_{J(pk)} = 150^\circ\text{C}$. T_C is variable depending on conditions. Second breakdown pulse limits are valid for duty cycles to 10% provided $T_{J(pk)} \leq 150^\circ\text{C}$. At high case temperatures, thermal limitations will reduce the power that can be handled to values less than the limitations imposed by second breakdown. (See AN415A)

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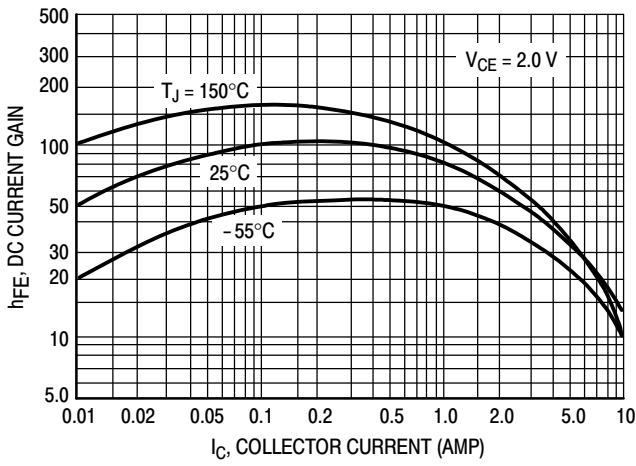


Figure 2. DC Current Gain

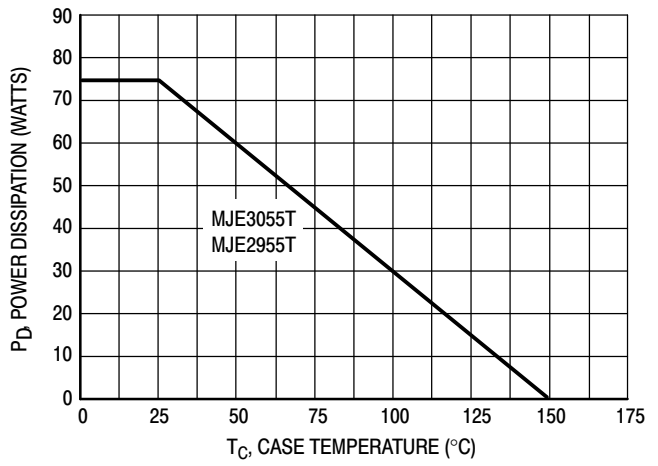


Figure 3. Power Derating

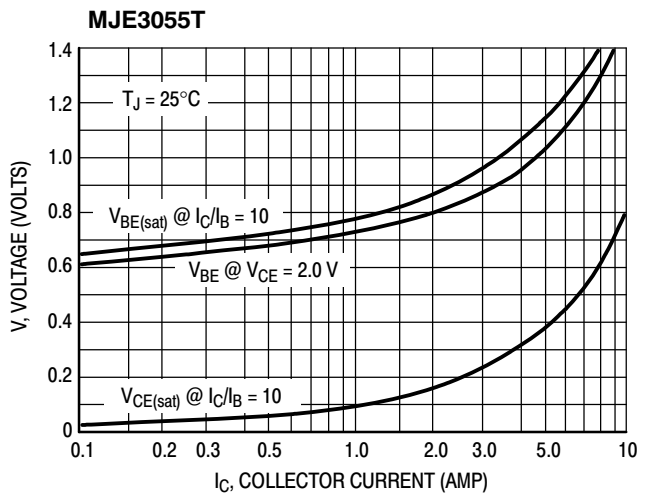
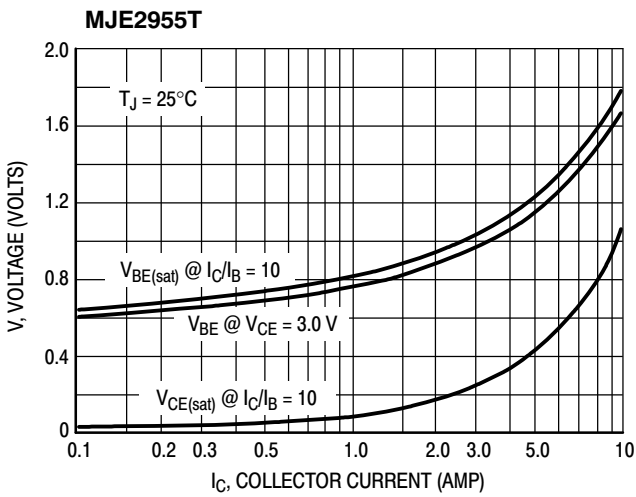


Figure 4. "On" Voltages

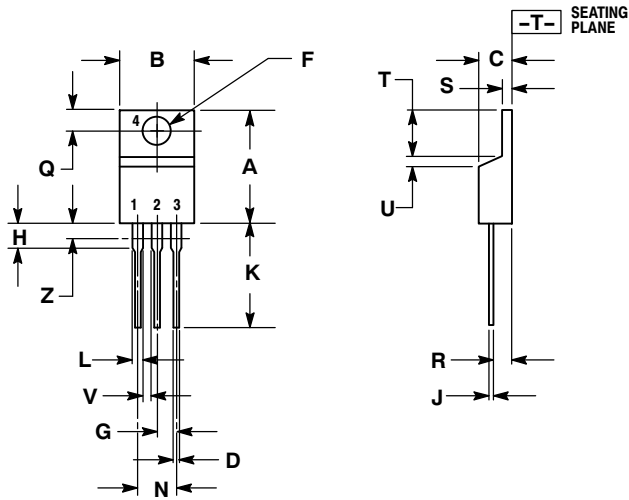
ORDERING INFORMATION

Device	Package	Shipping
MJE2955T	TO-220	50 Units / Rail
MJE2955TG	TO-220 (Pb-Free)	
MJE3055T	TO-220	
MJE3055TG	TO-220 (Pb-Free)	

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PACKAGE DIMENSIONS

TO-220
CASE 221A-09
ISSUE AE



NOTES:

1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH.
3. DIMENSION Z DEFINES A ZONE WHERE ALL BODY AND LEAD IRREGULARITIES ARE ALLOWED.

DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.570	0.620	14.48	15.75
B	0.380	0.405	9.66	10.28
C	0.160	0.190	4.07	4.82
D	0.025	0.035	0.64	0.88
F	0.142	0.161	3.61	4.09
G	0.095	0.105	2.42	2.66
H	0.110	0.155	2.80	3.93
J	0.014	0.025	0.36	0.64
K	0.500	0.562	12.70	14.27
L	0.045	0.060	1.15	1.52
N	0.190	0.210	4.83	5.33
Q	0.100	0.120	2.54	3.04
R	0.080	0.110	2.04	2.79
S	0.045	0.055	1.15	1.39
T	0.235	0.255	5.97	6.47
U	0.000	0.050	0.00	1.27
V	0.045	---	1.15	---
Z	---	0.080	---	2.04